

				Unit
				mA
				mA
				nA
				μ
C_{ies}	Input Capacitance	$V_{CE}=25V, V_{GE}=0V, f=1MHz$	26	nF
C				pF
$t_{(on)}$	Turn on DelayTime	$V_{CC}=300V, I_C=400A$ $R_G=1.5 \Omega$	$T_J=25$ 110 $T_J=125$ 120	ns ns
t_r	Rise Time	$V_{GE}=15V$ Inductive Load	$T_J=25$ 50 $T_J=125$ 60	ns ns
$t_{(off)}$	Turn off DelayTime	$V_{CC}=300V, I_C=400A$ $R_G=1.5 \Omega$	$T_J=25$ 490 $T_J=125$ 520	ns ns
t_f	Fall Time	$V_{GE}=15V$ Inductive Load	$T_J=25$ 60 $T_J=125$ 70	ns ns

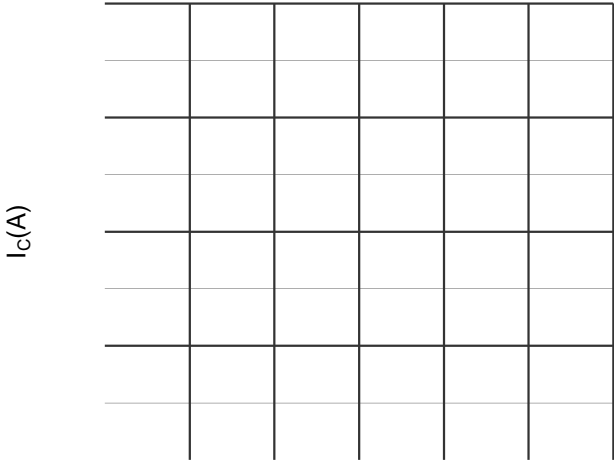


Figure 3. Typical Transfer characteristics IGBT-inverter

$E_{on} E_{off} (mJ)$

Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

J)

MMG400HB060B6EN

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$V_F(V)$

Figure 9. Diode Forward Characteristics Diode-inverter

⌋

R_g

Figure 10. Switching Energy vs Gate Resistor Diode-inverter

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Figure 14. Circuit Diagram